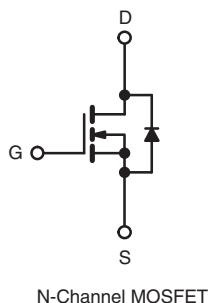
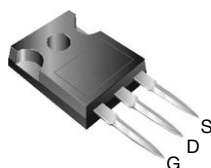


## D Series Power MOSFET

### PRODUCT SUMMARY

|                                         |                 |       |
|-----------------------------------------|-----------------|-------|
| $V_{DS}$ (V) at $T_J$ max.              | 550             |       |
| $R_{DS(on)}$ max. at 25 °C ( $\Omega$ ) | $V_{GS} = 10$ V | 0.150 |
| $Q_g$ max. (nC)                         | 96              |       |
| $Q_{gs}$ (nC)                           | 18              |       |
| $Q_{gd}$ (nC)                           | 29              |       |
| Configuration                           | Single          |       |

**TO-247AC**


### FEATURES

- Optimal Design
  - Low Area Specific On-Resistance
  - Low Input Capacitance ( $C_{iss}$ )
  - Reduced Capacitive Switching Losses
  - High Body Diode Ruggedness
  - Avalanche Energy Rated ( $U_{IS}$ )
- Optimal Efficiency and Operation
  - Low Cost
  - Simple Gate Drive Circuitry
  - Low Figure-Of-Merit (FOM):  $R_{on} \times Q_g$
  - Fast Switching
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

- Consumer Electronics
  - Displays (LCD or Plasma TV)
- Server and Telecom Power Supplies
  - SMPS
- Industrial
  - Welding, Induction Heating, Motor Drives
- Battery Chargers

### ORDERING INFORMATION

|                                 |                |
|---------------------------------|----------------|
| Package                         | TO-247AC       |
| Lead (Pb)-free                  | SiHG32N50D-E3  |
| Lead (Pb)-free and Halogen-free | SiHG32N50D-GE3 |

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

| PARAMETER                                        | SYMBOL           | LIMIT          | UNIT |
|--------------------------------------------------|------------------|----------------|------|
| Drain-Source Voltage                             | $V_{DS}$         | 500            | V    |
| Gate-Source Voltage                              | $V_{GS}$         | $\pm 30$       |      |
| Gate-Source Voltage AC ( $f > 1$ Hz)             |                  | 30             |      |
| Continuous Drain Current ( $T_J = 150$ °C)       | $V_{GS}$ at 10 V | $T_C = 25$ °C  | A    |
|                                                  |                  | $T_C = 100$ °C |      |
| Pulsed Drain Current <sup>a</sup>                | $I_{DM}$         | 89             |      |
| Linear Derating Factor                           |                  | 3.1            | W/°C |
| Single Pulse Avalanche Energy <sup>b</sup>       | $E_{AS}$         | 225            | mJ   |
| Maximum Power Dissipation                        | $P_D$            | 390            | W    |
| Operating Junction and Storage Temperature Range | $T_J, T_{stg}$   | - 55 to + 150  | °C   |
| Drain-Source Voltage Slope                       | $dV/dt$          | 24             | V/ns |
| Reverse Diode $dV/dt$ <sup>d</sup>               |                  | 0.37           |      |
| Soldering Recommendations (Peak Temperature)     | for 10 s         | 300°           | °C   |

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$  V, starting  $T_J = 25$  °C,  $L = 2.3$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 14$  A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$ , starting  $T_J = 25$  °C.

**THERMAL RESISTANCE RATINGS**

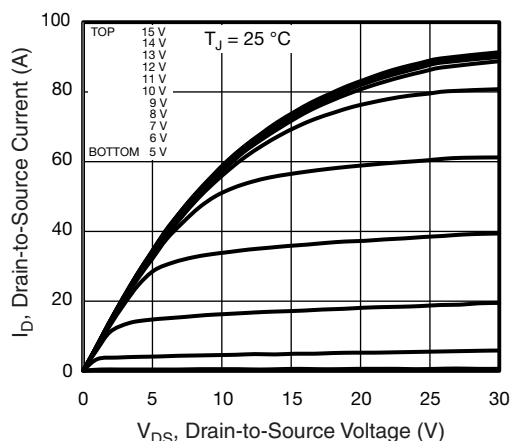
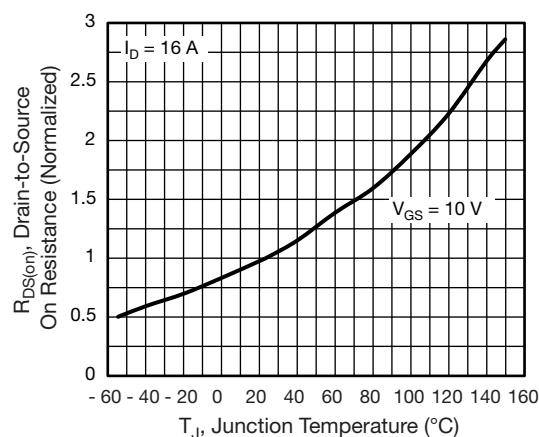
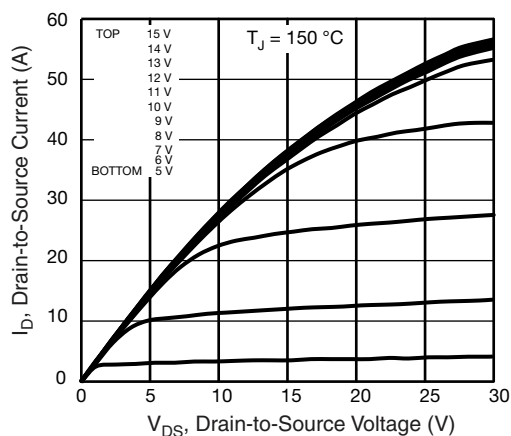
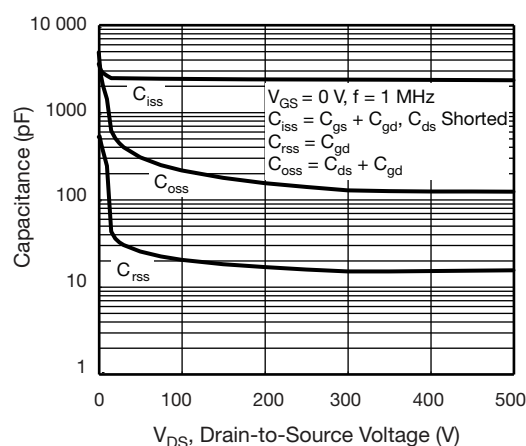
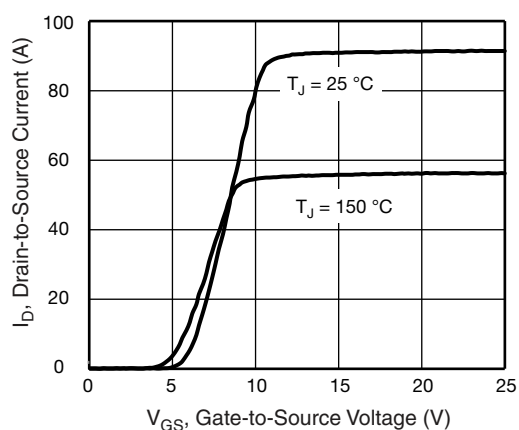
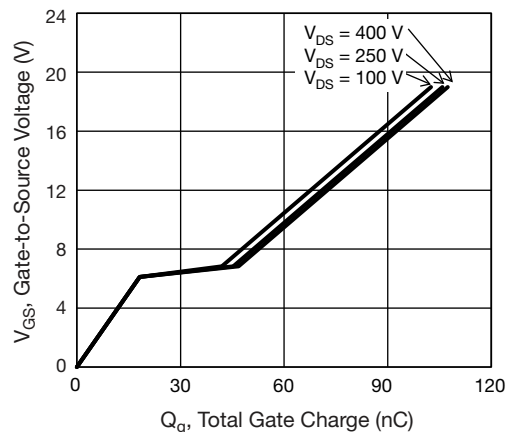
| PARAMETER                        | SYMBOL     | TYP. | MAX. | UNIT |
|----------------------------------|------------|------|------|------|
| Maximum Junction-to-Ambient      | $R_{thJA}$ | -    | 40   | °C/W |
| Maximum Junction-to-Case (Drain) | $R_{thJC}$ | -    | 0.32 |      |

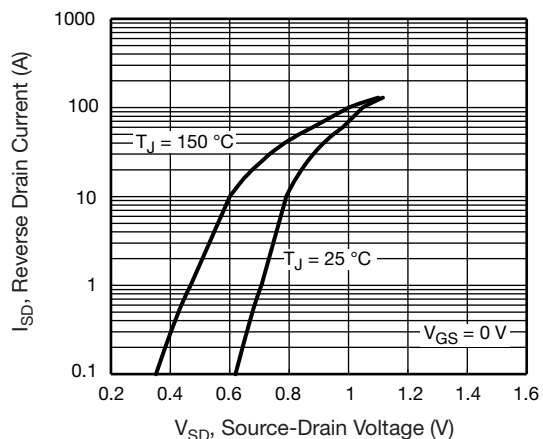
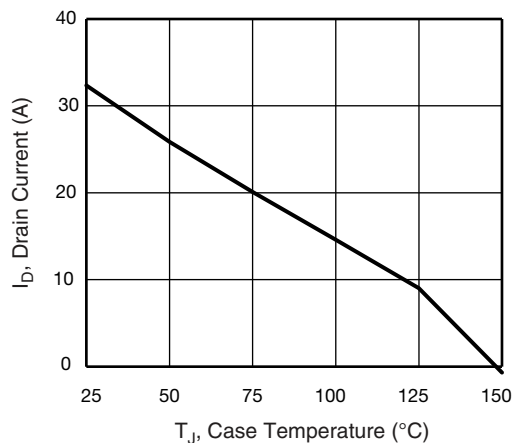
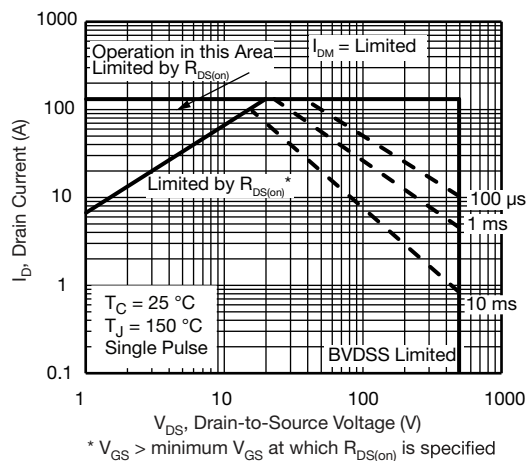
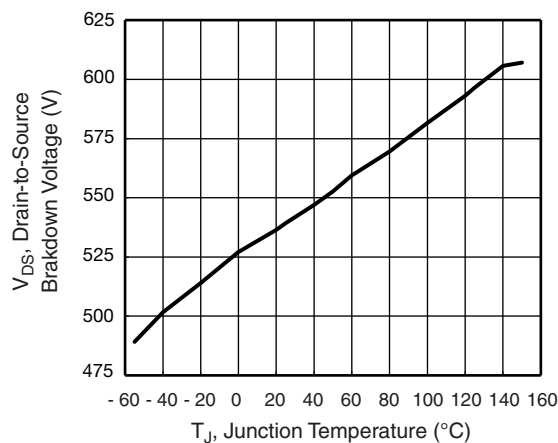
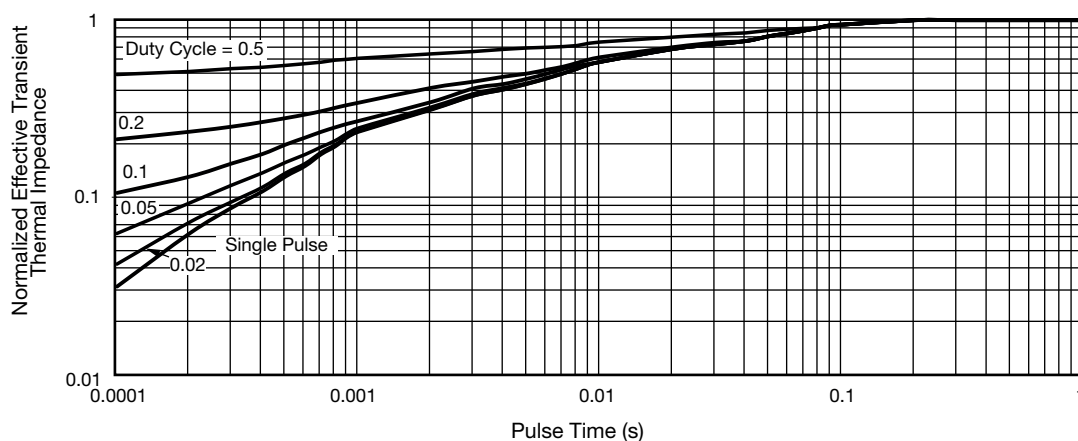
**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

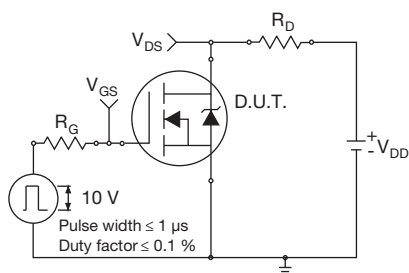
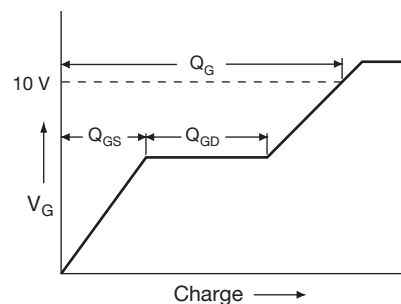
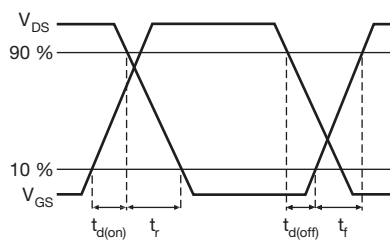
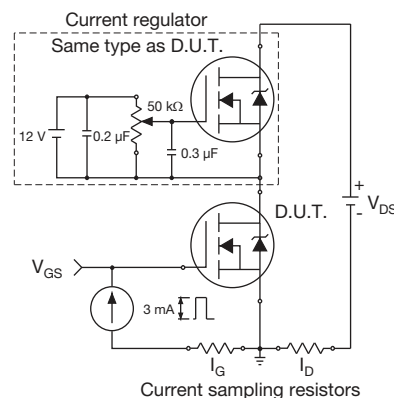
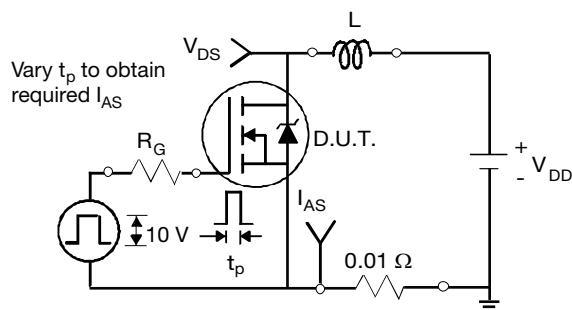
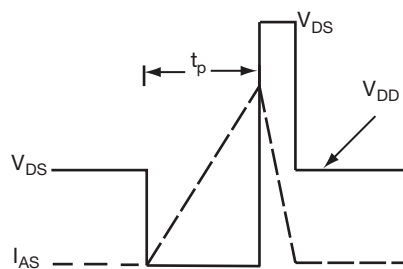
| PARAMETER                                                 | SYMBOL              | TEST CONDITIONS                                                                                                                                          | MIN. | TYP.  | MAX.      | UNIT          |
|-----------------------------------------------------------|---------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------|------|-------|-----------|---------------|
| <b>Static</b>                                             |                     |                                                                                                                                                          |      |       |           |               |
| Drain-Source Breakdown Voltage                            | $V_{DS}$            | $V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$                                                                                                   | 500  | -     | -         | V             |
| $V_{DS}$ Temperature Coefficient                          | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^{\circ}\text{C}$ , $I_D = 250\text{ }\mu\text{A}$                                                                               | -    | 0.6   | -         | V/°C          |
| Gate Threshold Voltage (N)                                | $V_{GS(th)}$        | $V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$                                                                                                       | 3.0  | -     | 5.0       | V             |
| Gate-Source Leakage                                       | $I_{GSS}$           | $V_{GS} = \pm 30\text{ V}$                                                                                                                               | -    | -     | $\pm 100$ | nA            |
| Zero Gate Voltage Drain Current                           | $I_{DSS}$           | $V_{DS} = 500\text{ V}$ , $V_{GS} = 0\text{ V}$                                                                                                          | -    | -     | 1         | $\mu\text{A}$ |
|                                                           |                     | $V_{DS} = 400\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125\text{ }^{\circ}\text{C}$                                                                    | -    | -     | 10        |               |
| Drain-Source On-State Resistance                          | $R_{DS(on)}$        | $V_{GS} = 10\text{ V}$ , $I_D = 16\text{ A}$                                                                                                             | -    | 0.125 | 0.150     | $\Omega$      |
| Forward Transconductance <sup>a</sup>                     | $g_{fs}$            | $V_{DS} = 50\text{ V}$ , $I_D = 16\text{ A}$                                                                                                             | -    | 11    | -         | S             |
| <b>Dynamic</b>                                            |                     |                                                                                                                                                          |      |       |           |               |
| Input Capacitance                                         | $C_{iss}$           | $V_{GS} = 0\text{ V}$ ,<br>$V_{DS} = 100\text{ V}$ ,<br>$f = 1\text{ MHz}$                                                                               | -    | 2550  | -         | pF            |
| Output Capacitance                                        | $C_{oss}$           |                                                                                                                                                          | -    | 225   | -         |               |
| Reverse Transfer Capacitance                              | $C_{rss}$           |                                                                                                                                                          | -    | 21    | -         |               |
| Effective Output Capacitance, Energy Related <sup>a</sup> | $C_{o(er)}$         | $V_{GS} = 0\text{ V}$ , $V_{DS} = 0\text{ V to } 400\text{ V}$                                                                                           | -    | 190   | -         |               |
| Effective Output Capacitance, Time Related <sup>b</sup>   | $C_{o(tr)}$         |                                                                                                                                                          | -    | 279   | -         |               |
| Total Gate Charge                                         | $Q_g$               | $V_{GS} = 10\text{ V}$ ,<br>$I_D = 16\text{ A}$ , $V_{DS} = 400\text{ V}$                                                                                | -    | 64    | 96        | nC            |
| Gate-Source Charge                                        | $Q_{gs}$            |                                                                                                                                                          | -    | 18    | -         |               |
| Gate-Drain Charge                                         | $Q_{gd}$            |                                                                                                                                                          | -    | 29    | -         |               |
| Turn-On Delay Time                                        | $t_{d(on)}$         | $V_{DD} = 400\text{ V}$ , $I_D = 16\text{ A}$ ,<br>$V_{GS} = 10\text{ V}$ , $R_g = 9.1\text{ }\Omega$                                                    | -    | 27    | 54        | ns            |
| Rise Time                                                 | $t_r$               |                                                                                                                                                          | -    | 75    | 113       |               |
| Turn-Off Delay Time                                       | $t_{d(off)}$        |                                                                                                                                                          | -    | 58    | 87        |               |
| Fall Time                                                 | $t_f$               |                                                                                                                                                          | -    | 55    | 83        |               |
| Gate Input Resistance                                     | $R_g$               | $f = 1\text{ MHz}$ , open drain                                                                                                                          | -    | 1.5   | -         | $\Omega$      |
| <b>Drain-Source Body Diode Characteristics</b>            |                     |                                                                                                                                                          |      |       |           |               |
| Continuous Source-Drain Diode Current                     | $I_S$               | MOSFET symbol showing the integral reverse p - n junction diode<br> | -    | -     | 32        | A             |
| Pulsed Diode Forward Current                              | $I_{SM}$            |                                                                                                                                                          | -    | -     | 128       |               |
| Diode Forward Voltage                                     | $V_{SD}$            | $T_J = 25\text{ }^{\circ}\text{C}$ , $I_S = 16\text{ A}$ , $V_{GS} = 0\text{ V}$                                                                         | -    | -     | 1.2       | V             |
| Reverse Recovery Time                                     | $t_{rr}$            | $T_J = 25\text{ }^{\circ}\text{C}$ , $I_F = I_S = 16\text{ A}$ ,<br>$dI/dt = 100\text{ A}/\mu\text{s}$ , $V_R = 20\text{ V}$                             | -    | 467   | -         | ns            |
| Reverse Recovery Charge                                   | $Q_{rr}$            |                                                                                                                                                          | -    | 7     | -         | $\mu\text{C}$ |
| Reverse Recovery Current                                  | $I_{RRM}$           |                                                                                                                                                          | -    | 28    | -         | A             |

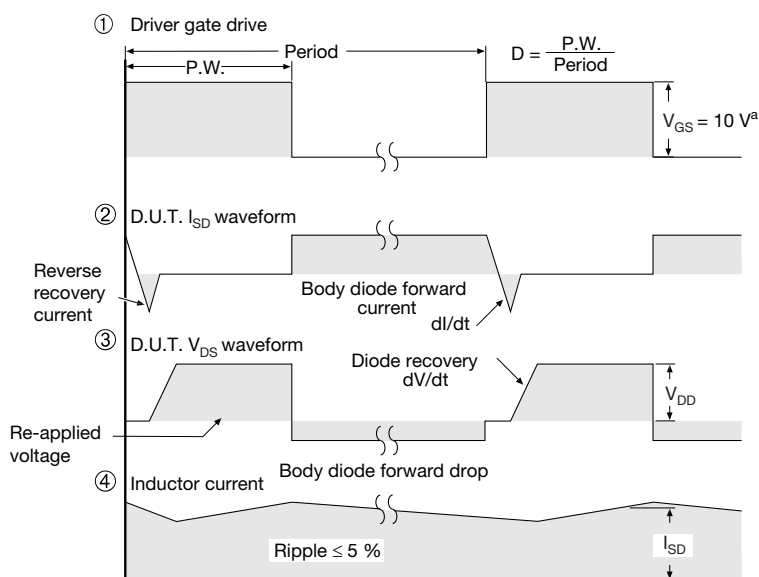
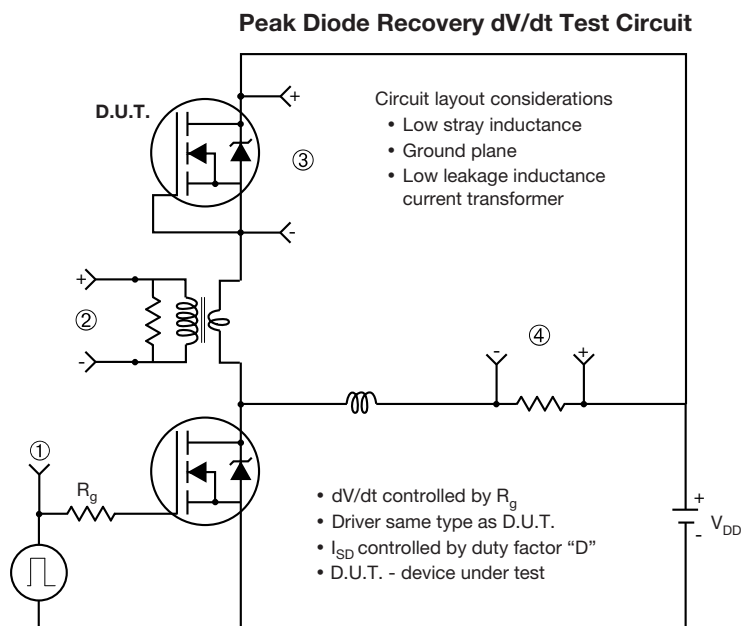
**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .  
b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 4 - Normalized On-Resistance vs. Temperature**

**Fig. 2 - Typical Output Characteristics**

**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**


**Fig. 7 - Typical Source-Drain Diode Forward Voltage**

**Fig. 9 - Maximum Drain Current vs. Case Temperature**

**Fig. 8 - Maximum Safe Operating Area**

**Fig. 10 - Temperature vs. Drain-to-Source Voltage**

**Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case**


**Fig. 12 - Switching Time Test Circuit**

**Fig. 16 - Basic Gate Charge Waveform**

**Fig. 13 - Switching Time Waveforms**

**Fig. 17 - Gate Charge Test Circuit**

**Fig. 14 - Unclamped Inductive Test Circuit**

**Fig. 15 - Unclamped Inductive Waveforms**


**Note**

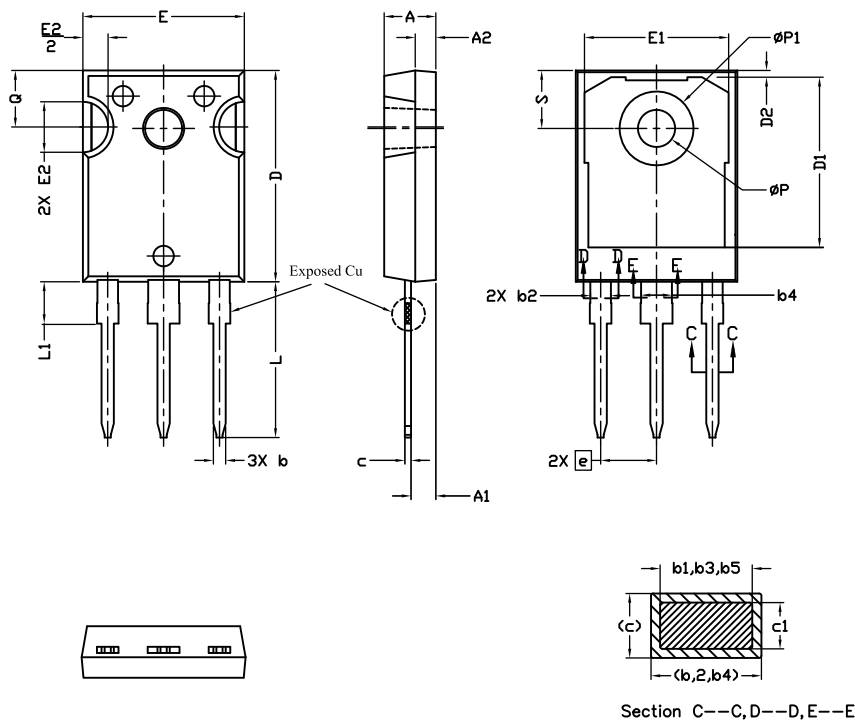
a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 18 - For N-Channel**

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## TO-247AC (High Voltage)

**VERSION 1: FACILITY CODE = 9**


| MILLIMETERS |       |       |       |
|-------------|-------|-------|-------|
| DIM.        | MIN.  | MAX.  | NOTES |
| A           | 4.83  | 5.21  |       |
| A1          | 2.29  | 2.55  |       |
| A2          | 1.50  | 2.49  |       |
| b           | 1.12  | 1.33  |       |
| b1          | 1.12  | 1.28  |       |
| b2          | 1.91  | 2.39  | 6     |
| b3          | 1.91  | 2.34  |       |
| b4          | 2.87  | 3.22  | 6, 8  |
| b5          | 2.87  | 3.18  |       |
| c           | 0.55  | 0.69  | 6     |
| c1          | 0.55  | 0.65  |       |
| D           | 20.40 | 20.70 | 4     |

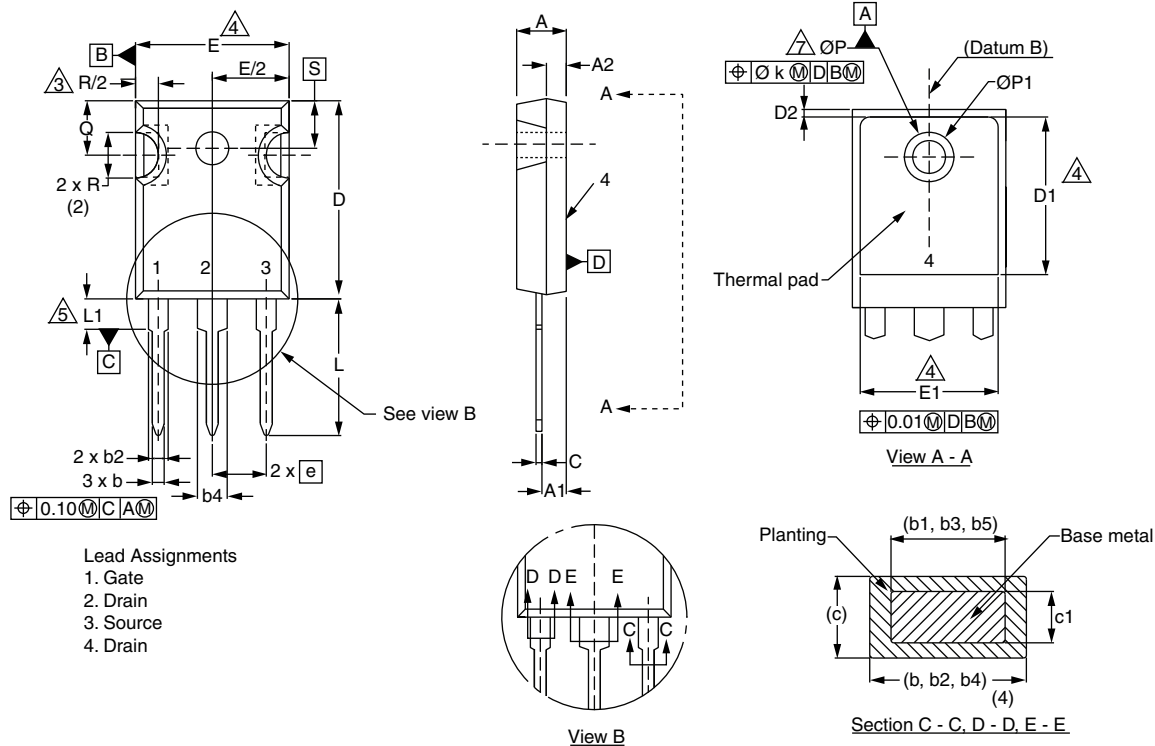
| MILLIMETERS |           |       |       |
|-------------|-----------|-------|-------|
| DIM.        | MIN.      | MAX.  | NOTES |
| D1          | 16.25     | 16.85 | 5     |
| D2          | 0.56      | 0.76  |       |
| E           | 15.50     | 15.87 | 4     |
| E1          | 13.46     | 14.16 | 5     |
| E2          | 4.52      | 5.49  | 3     |
| e           | 5.44 BSC  |       |       |
| L           | 14.90     | 15.40 |       |
| L1          | 3.96      | 4.16  | 6     |
| Ø P         | 3.56      | 3.65  | 7     |
| Ø P1        | 7.19 ref. |       |       |
| Q           | 5.31      | 5.69  |       |
| S           | 5.54      | 5.74  |       |

### Notes

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition



## VERSION 2: FACILITY CODE = Y



| DIM. | MILLIMETERS |       | NOTES |
|------|-------------|-------|-------|
|      | MIN.        | MAX.  |       |
| A    | 4.58        | 5.31  |       |
| A1   | 2.21        | 2.59  |       |
| A2   | 1.17        | 2.49  |       |
| b    | 0.99        | 1.40  |       |
| b1   | 0.99        | 1.35  |       |
| b2   | 1.53        | 2.39  |       |
| b3   | 1.65        | 2.37  |       |
| b4   | 2.42        | 3.43  |       |
| b5   | 2.59        | 3.38  |       |
| c    | 0.38        | 0.86  |       |
| c1   | 0.38        | 0.76  |       |
| D    | 19.71       | 20.82 |       |
| D1   | 13.08       | -     |       |

| DIM. | MILLIMETERS |       | NOTES |
|------|-------------|-------|-------|
|      | MIN.        | MAX.  |       |
| D2   | 0.51        | 1.30  |       |
| E    | 15.29       | 15.87 |       |
| E1   | 13.72       | -     |       |
| e    | 5.46 BSC    |       |       |
| Ø k  | 0.254       |       |       |
| L    | 14.20       | 16.25 |       |
| L1   | 3.71        | 4.29  |       |
| Ø P  | 3.51        | 3.66  |       |
| Ø P1 | -           | 7.39  |       |
| Q    | 5.31        | 5.69  |       |
| R    | 4.52        | 5.49  |       |
| S    | 5.51 BSC    |       |       |

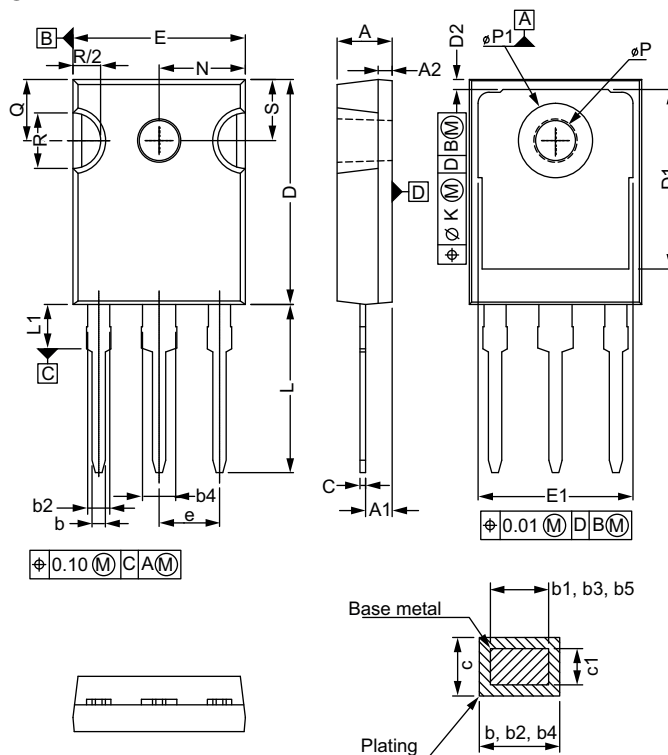
### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c





## VERSION 3: FACILITY CODE = N



| MILLIMETERS |       |       |
|-------------|-------|-------|
| DIM.        | MIN.  | MAX.  |
| A           | 4.65  | 5.31  |
| A1          | 2.21  | 2.59  |
| A2          | 1.17  | 1.37  |
| b           | 0.99  | 1.40  |
| b1          | 0.99  | 1.35  |
| b2          | 1.65  | 2.39  |
| b3          | 1.65  | 2.34  |
| b4          | 2.59  | 3.43  |
| b5          | 2.59  | 3.38  |
| c           | 0.38  | 0.89  |
| c1          | 0.38  | 0.84  |
| D           | 19.71 | 20.70 |
| D1          | 13.08 | -     |

| MILLIMETERS |          |       |
|-------------|----------|-------|
| DIM.        | MIN.     | MAX.  |
| D2          | 0.51     | 1.35  |
| E           | 15.29    | 15.87 |
| E1          | 13.46    | -     |
| e           | 5.46 BSC |       |
| k           | 0.254    |       |
| L           | 14.20    | 16.10 |
| L1          | 3.71     | 4.29  |
| N           | 7.62 BSC |       |
| P           | 3.56     | 3.66  |
| P1          | -        | 7.39  |
| Q           | 5.31     | 5.69  |
| R           | 4.52     | 5.49  |
| S           | 5.51 BSC |       |

ECN: E20-0545-Rev. F, 19-Oct-2020  
DWG: 5971

### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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